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A journal devoted to the properties of interfaces
in relation to the synthesis and behaviour of materials



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A JOURNAL DEVOTED TO THE PROPERTIES OF INTERFACES
IN RELATION TO THE SYNTHESIS AND BEHAVIOUR OF MATERIALS

Editors:

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Master Index to Volumes 51-61



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- Compañó, R., U. del Pennino, C. Mariani, M. Grazia Betti and M. Pedio, Bi-induced electronic states at the interface with n- and p-type GaAs(110) 56-58 (1992) 242
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- Evans, D.A., T.P. Chen, Th. Chassé and K. Horn, The interaction of platinum with GaP(110): band bending and surface photovoltage effects 56-58 (1992) 233
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- Fujieda, S., E. Benoit and T. Baba, Electrical properties of SiN_x /thin-Si-interlayer/GaAs MIS systems ruled by surface superstructures of GaAs and crystallinity of Si interlayers 60/61 (1992) 716
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- Fujisaki, Y., Control of the GaAs/ SiO_2 interface through sulfur passivation and a photo-CVD process 54 (1992) 95
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- Fukuda, H., M. Yasuda, T. Iwabuchi and S. Ohno, Characterization of SiO_2 /Si(100) interface structure of N_2O -oxynitrided ultrathin SiO_2 films 60/61 (1992) 359
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- Glachant, A., P. Soukiasian, P.S. Mangat, J. Peng and S.T. Kim, Photoinduced oxynitride formation on semiconductors: NO on Si(111)2 × 1 56-58 (1992) 802

- Gladkov, P., K. Varblianska, Ts. Marinova, V. Krastev and J. Stoemenos, Characterization of thermally oxidized Ta/GaAs Schottky barrier structures prepared by low energy RF sputtering with X-ray photoemission, TEM and optical transmittance measurements 59 (1992) 179
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- Golusda, E., R. Lange, K.-D. Lühmann, G. Mollekopf, M. Wacker and H. Stafast, CW CO₂ laser CVD of amorphous hydrogenated silicon (a-Si:H): influence of the deposition geometry 54 (1992) 30
- Gomeniuk, Yu.V., R.N. Litovski, V.S. Lysenko, I.N. Osiyuk and I.P. Tyagulski, Thermally stimulated field emission of charge from traps in the transition layer of Si-SiO₂ structures 55 (1992) 179
- Gomeniuk, Yu.V., R.N. Litovski, V.S. Lysenko, I.N. Osiyuk and I.P. Tyagulski, Current stochasticity of field emission of charge from traps in the transition layer of implanted MIS structures 59 (1992) 91
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- González, P., E. García, J. Pou, D. Fernández, B. León and M. Pérez-Amor, Excimer laser CVD of silicon oxide on GaAs: a comparison with deposition on c-Si 54 (1992) 108
- González, P., see Fernández, D. 54 (1992) 112
- González-Elipé, A.R., R. Alvarez, J.P. Holgado, J.P. Espinos, G. Munuera and J.M. Sanz, An XPS study of the Ar⁺-induced reduction of Ni²⁺ in NiO and Ni-Si oxide systems 51 (1991) 19
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- Groenen, P.A.C., J.G.A. Hölscher and H.H. Brongersma, The WF₆-Si reaction studied in situ by time-resolved mass spectrometry 53 (1991) 30
- Gröning, P., S. Nowak and L. Schlappbach, Temperature-dependent surface modifications of AISI 316L and AISI 440C stainless steel substrates 52 (1991) 333
- Guarnieri, C.R., F.M. d'Heurle, J.J. Cuomo and S.J. Whitehair, Reaction of niobium with diamond films 53 (1991) 115
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- Guyaux, J.L., A. Degiovanni, P.A. Thiry, R. Sporken and R. Caudano, Investigation of the AlAs-GaAs interface by high resolution electron energy loss spectroscopy 56-58 (1992) 697

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- Higo, M., K. Nishino and S. Kamata, Characterization of evaporated silicon films by inelastic electron tunneling spectroscopy 51 (1991) 61
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- GaAs(001) surfaces with different superstructures 56-58 (1992) 11
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- Hopfe, V., A. Tehel, A. Baier and J. Scharsig, IR-laser CVD of TiB_2 , TiC_x and TiC_xN_y coatings on carbon fibres 54 (1992) 78
- Hopfmann, Ch., Ch. Werner and J.I. Ulacia F., Numerical analysis of fluid flow and nonuniformities in a polysilicon LPCVD batch reactor 52 (1991) 169
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- Horng, S., Y. Hirose, A. Kahn, C. Wrenn and R. Pfeffer, $\text{Ca}_{0.5}\text{Sr}_{0.5}\text{F}_2/\text{GaAs}$ (100) for epitaxial regrowth and electron-beam patterning 56-58 (1992) 855
- Hosaka, S., see Hosoki, S. 60/61 (1992) 643
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- Hricovini, K., G. Le Lay, A. Kahn, A. Taleb-Ibrahimi and J.E. Bonnet, Initial stages of Schottky-barrier formation of Bi/Si(111) and Bi/Si(100) interfaces 56-58 (1992) 259
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- Hultquist, G., M. Seo, Q. Lu, G.K. Chuah and K.L. Tan, Surface reactions at 300-750 K in the iron-oxygen-water system studied by SIMS 59 (1992) 135
- Hunger, E., H. Pietsch, S. Petzoldt and E. Matthias, Multishot ablation of polymer and metal films at 248 nm 54 (1992) 227
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- Ibrahim, M.M., F.M. El-Hossary, N.Z. Negm, M. Abed and R.E. Ricker, Effect of RF plasma nitriding time on microhardness and corrosion resistance of 304 stainless steel 59 (1992) 253
- Ichikawa, M. and T. Doi, Microprobe RHEED study of electromigration effect on Si MBE growth 60/61 (1992) 45
- Ichikawa, Y., H. Adachi, K. Setsune and K. Wasa, Epitaxial growth of $\text{Bi}_4\text{Ti}_3\text{O}_{12}$ thin films by dual ion-beam sputtering 60/61 (1992) 749
- Igari, Y., see Kusunoki, I. 59 (1992) 95
- Ihara, S., T. Uda and M. Hirao, Electronic structure of a dimer-adatom-stacking-fault model for the Si(111) 7×7 reconstructed surface 60/61 (1992) 22
- Ihlemann, J., Excimer laser ablation of fused silica 54 (1992) 193
- Iida, S., Y. Hidemura, K. Higashimukai and S. Nagata, In situ observation of resistivity oscillation at the Ti/insulator interface 56-58 (1992) 811
- Iida, S., Y. Hidemura, K. Higashimukai

- and S. Nagata, Thermal reactions of thin Ti films with sapphire substrates 56-58 (1992) 816
- Ijdiyaou, Y., M. Azizan, E.L. Ameziane, M. Brunel and T.A. Nguyen Tan, On the formation of molybdenum silicides in Mo-Si multilayers: the effect of Mo thickness and annealing temperature 55 (1992) 165
- Illmann, U., see Reisse, G. 54 (1992) 84
- Imai, F., H. Kuramochi, K. Kunitomi, T. Uchijima, H. Kondoh, H. Shindo, C. Nishihara, M. Kaise and H. Nozoye, Synthesis of MgO/TiO_x superlattices 60/61 (1992) 770
- Imai, S., see Ueno, T. 56-58 (1992) 27
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- Lebland, F., C. Licoppe, Y. Gao, Y.I. Nissim and S. Rigo, Rapid thermal chemical vapour deposition of SiO_xN_y films 54 (1992) 125
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- Leusink, G.J., T.G.M. Oosterlaken, C.A. van der Jeugd, G.C.A.M. Janssen and S. Radelaar, The growth of ultra-thin amorphous WGe_x films on Si by the GeH_4 reduction of WF_6 53 (1991) 47
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- Licoppe, C., C. Meriadec, Y.I. Nissim and J.M. Moison, Surface mechanisms in the UVCVD of SiO_2 films 54 (1992) 445
- Licoppe, C., C. Debauche, F. Houzay, J. Flicstein, Y.I. Nissim and J.M. Moison, Differences in the SiO_2/InP interfaces obtained by thermal and UV-induced chemical vapour deposition 56-58 (1992) 789
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- Thomas, O., G. Scilla, P. Gas, J. Cotte, R.V. Joshi, M. Bakli, G. Göltz and F.M. d'Heurle, Diffusion of dopants in tungsten disilicide: effects of diffusion paths 53 (1991) 165
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- Lagomarsino, F. Scarinci, P. Castucci, C. Giannini, E. Fontes and J.R. Patel 56-58 (1992) 402
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55 (1992) 11

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- Grain boundary composition of pure and boron-doped cobalt disilicide, A. Malchère, P. Gas, C. Haut, A. Larere, T.T. Nguyen and S. Poize 53 (1991) 132
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- leri, M.G. Lancellotti, A. di Bona, G. Granozzi and G.A. Rizzi 56-58 (1992) 205
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- Chemical shifts of the O 1s core levels for oxygen dimers in YBa₂Cu₃O_{7-δ}: cluster DVM-X α calculations, G.L. Gutsev, Yu.M. Shul'ga and V.I. Rubtsov 52 (1991) 329
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- Si(001) vicinal surface oxidation in O_2 : angle-resolved Si2p core-level study using synchrotron radiation, F. Rochet, H. Roulet, G. Dufour, S. Carniato, C. Guillot, N. Barrett and M. Froment 59 (1992) 117
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- Initial growth of Ge films on Si(111) 7×7 surfaces by gas source molecular beam epitaxy, N. Ohshima, S. Zaima, Y. Koide, S. Tomioka and Y. Yasuda 60/61 (1992) 120
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- Elementary processes in the MBE growth of GaAs, B.A. Joyce, T. Shitara, A. Yoshinaga, D.D. Vvedensky, J.H. Neave and J. Zhang 60/61 (1992) 200
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- ### Electron microscopy
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- Optical characterization of porous silicon layers formed on heavily p-doped substrates, H. Münder, C. Andrzejak,

- M.G. Berger, T. Eickhoff, H. Lüth, W. Theiss, U. Rossow, W. Richter, R. Herino and M. Ligeon 56-58 (1992) 6
- In situ monitoring of heterostructure growth by optical spectroscopies: CdS on InP(110), D.R.T. Zahn, Ch. Maierhofer, A. Winter, M. Reckzügel, R. Srama, U. Rossow, A. Thomas, K. Horn and W. Richter 56-58 (1992) 684
- ### Epitaxy
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- Early stages of heteroepitaxial growth of ZnSe on GaAs by MOVPE, MOASE and MBE, J.E. Palmer, S. Tohno, Y. Kawaguchi and S. Zembutsu 60/61 (1992) 266
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- Raman scattering in GaP/AlP short-period superlattices grown by gas source molecular beam epitaxy, R.K. Soni, H. Asahi, S. Emura, T. Watanabe, K. Asami and S. Gonda 60/61 (1992) 553
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- Control of rotational twins in a SOI-GaAs film grown on surface modified fluoride/Si(111), A. Ono, K. Tsutsui and S. Furukawa 60/61 (1992) 608
- Gas source MEE growth of InGaAs/InP superlattices, H. Asahi, T. Kohara, R.K. Soni, N. Takeyasu, K. Asami, S. Emura and S. Gonda 60/61 (1992) 625
- Evaluation of nucleation and defects in MBE-grown strained InAs/GaAs quantum structures on variously oriented substrates, A. Suzuki, J. Lee, K. Kudo, Y. Makita, A. Yamada and K. Tanaka 60/61 (1992) 631
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- Atomic layer growth of TiO₂ on silica, E.-L. Lakomaa, S. Haukka and T. Suntola 60/61 (1992) 742
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- MBE growth and magneto-optic properties of magnetic multilayers, C.M. Falco and B.N. Engel 60/61 (1992) 790
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- Optical second harmonic generation from the Si(111)-Ga interface, P.V. Kelly, J.D. O'Mahony, J.F. McGilp and Th. Rasing 56-58 (1992) 453
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- Passivation of shallow donors in GaAs by oxygen plasma exposure, I. Thurzo, E. Pinčík, L. Harmatha, V. Nágl and M. Gaži 52 (1991) 311
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- Laser-surface diagnostics of GaAs growth processes. I. The influence of surface contamination upon optical second harmonic generation from GaAs (100) surfaces, M.E. Pemble, A. Stafford and A.G. Taylor 54 (1992) 490
- Laser-surface diagnostics of GaAs growth processes. II. Reflectance anisotropy studies of GaAs growth by MBE, S.R. Armstrong, M.E. Pemble, A.G. Taylor, B.A. Joyce, J.H. Neave, J. Zhang and D.A. Klug 54 (1992) 493
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- Nucleation and growth of gallium arsenide on silicon, B. Bartenlian, R. Bisaro, J. Olivier, J.-P. Hirtz, M. Pitaval, J. Meddeb and A. Rocher 56-58 (1992) 589
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- Influence of strain on structural and vibrational properties of (InAs)_m(GaAs)_n strained superlattices grown by molecular beam epitaxy, G. Scamarcio, O. Brandt, L. Tapfer and K. Ploog 56-58 (1992) 610
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- by CBED, H. Gong and F.W. Schapink 56-58 (1992) 643
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- Auger sputtering profiling of an $\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}/\text{GaAs}$ superlattice grown by molecular beam epitaxy, G. Cossu, G.M. Ingo, G. Mattogno, G. Padeletti and S. Viticoli 56-58 (1992) 708
- Internally detected electron photoexcitation spectroscopy on heterostructures, C. Coluzza, A. Neglia, A. Bennouna, M. Capizzi, R. Carluccio, A. Frova and P.C. Srivastava 56-58 (1992) 733
- The effect of germanium bilayers on the band offsets at the InAs-GaAs interface, T.-H. Shen and C.C. Matthai 56-58 (1992) 746
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- Chemical and electronic properties of aluminum nitride on GaAs(110), H.-U. Baier and W. Mönch 56-58 (1992) 766
- Rb- and K-promoted nitridation of cleaved GaAs and InP surfaces at room temperature, P. Soukiassian, H.I. Starnberg and T. Kendelewicz 56-58 (1992) 772
- A novel passivation technique of GaAs power MESFETs, M. Taniguchi, T. Murakawa and Y. Kajitani 56-58 (1992) 827
- $\text{Ca}_{0.5}\text{Sr}_{0.5}\text{F}_2/\text{GaAs}$ (100) for epitaxial regrowth and electron-beam patterning, S. Horng, Y. Hirose, A. Kahn, C. Wrenn and R. Pfeffer 56-58 (1992) 855
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- First-principles calculation of the migration energy of a Ga adatom on an As-stabilized GaAs(001) surface, K. Shiraishi 60/61 (1992) 210
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- ### Glass
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- Hydrogen-induced reordering of the Si(111)- $\sqrt{3} \times \sqrt{3}$ -Al surface studied by ERDA/LEED, M. Naitoh, H. Ohnishi, Y. Ozaki, F. Shoji and K. Oura 60/61 (1992) 190

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- Heteroepitaxial growth of strained and relaxed layers of InAs on InP investigated by RHEED and HRTEM, G. Hollinger, M. Gendry, J.L. Duvault, C. Santinelli, P. Ferret, C. Miossi and M. Pitaval 56-58 (1992) 665
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- ### Indium oxide
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- ### Indium phosphide
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- Photoinduced oxynitride formation on semiconductors: NO on Si(111)2 × 1, A. Glachant, P. Soukiassian, P.S. Mangat, J. Peng and S.T. Kim 56-58 (1992) 802
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- ### Iridium
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- ### Lead
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- ### Methane
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- ### Nitrides
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- ### Nitrogen
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- ### Selenium
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54 (1992) 125

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Adhesion	Cobalt oxide
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Alkali metals	Copper
Alloys	Corrosion
Aluminium	Crystallization
Aluminium oxide	Cuprous oxide
Ammonia	
Amorphous materials	Diamond
Annealing	Dielectric constant
Antimony	Diffusion
Arsenic	Doping effects
Atomic force microscopy	
Auger electron spectroscopy	Electrical measurements
	Electrical properties
Band structure	Electron bombardment
Barium	Electron diffraction
Beryllium	Electron energy loss spectroscopy
Bismuth	Electron microscopy
Borides	Electron spin resonance
Boron	Electron stimulated desorption
Boron nitride	Ellipsometry
	Epitaxy
Cadmium selenide	Etching
Cadmium sulphide	Evaporation
Cadmium telluride	
Carbides	Field emission
Carbon	Field emission microscopy
Carbon monoxide	Field ion microscopy
Carboxylic acid	Field ionisation
Catalysis	
Cathodes	Gallium
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Chemisorption theory	Gallium selenide
Chromium	Germanium
Clusters	Glass
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- Grain boundary
Graphite

Halides
Hall effect
Halogenides
Halogens
Heterostructures
Hydrides
Hydrocarbons
Hydrogen
Hydrogen sulphide

Indium
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Infrared spectroscopy
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Insulator-semiconductor interfaces
Interfaces
Ion bombardment
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Lanthanides
Laser processing
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Mass spectroscopy
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Metal-oxide-semiconductor structure (MOS)
Metals
Metal-semiconductor interfaces
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Molecular beam epitaxy

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Optical properties
Organic substances
Organometallic vapour deposition
Oxidation
Oxides
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Ozone

Palladium
Phosphine
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Photoconductivity
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Photoelectron spectroscopy
Photon emission
Plasma processing
Platinum
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Quantum effects

Radiation damage
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Rhenium
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Scandium
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Second harmonic generation
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Selenium

- Semiconductors
- Semiconductor-semiconductor interfaces
- Silane
- Silicides
- Silicon
- Silicon carbide
- Silicon nitride
- Silicon oxide
- Silver
- Sintering
- Solid-electrolyte interface
- Solid phase epitaxy
- Sputter deposition
- Sputtering
- Steel
- Sulphides
- Sulphur
- Superconductivity
- Superlattices
- Surface and interface states
- Surface composition
- Surface defects
- Surface diffusion
- Surface energy
- Surface morphology
- Surface phonons and adsorbate vibrations
- Surface photovoltage
- Surface plasmons
- Surface roughness
- Surface segregation
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- Surface thermodynamics
- Tantalum
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- Thermal desorption
- Thin films
- Tin
- Tin oxide
- Titanium
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- X-ray absorption
- X-ray diffraction
- X-ray emission
- X-ray scattering
- X-ray spectroscopy
- Zeolites
- Zinc
- Zirconium

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- [3] F.J. Himpsel, *Surf. Sci. Rep.* 12 (1990) 1.
- [4] A. Roth, *Vacuum Technology*, 3rd ed. (North-Holland, Amsterdam, 1990).
- [5] V. Celli, in: *Dynamical Properties of Solids*, Vol. 6, Eds. G.K. Horton and A.A. Maradudin (North-Holland, Amsterdam, 1990) p. 337.

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I (cap.), l (el), 1 (one), ' (prime)	c, C; k, K, κ (kappa); p, P, ρ (rho)
o (lower case), O (cap.), 0 (zero), $^{\circ}$ (deg)	u, v (lower case), ν (nu), V (cap.)
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